

June 2009

FDZ193P

P-Channel 1.7V PowerTrench® WL-CSP MOSFET

-20V, -1A, $90m\Omega$

Features

- Max $r_{DS(on)}$ = 90m Ω at V_{GS} = -4.5V, I_D = -1A
- Max $r_{DS(on)}$ = 130m Ω at V_{GS} = -2.5V, I_D = -1A
- Max $r_{DS(on)}$ = 300m Ω at V_{GS} = -1.7V, I_D = -1A
- Occupies only 1.5 mm² of PCB area Less than 50% of the area of 2 x 2 BGA
- Ultra-thin package: less than 0.65 mm height when mounted to PCB
- RoHS Compliant

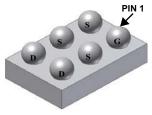


General Description

Designed on Fairchild's advanced 1.7V PowerTrench® process with state of the art "low pitch" WLCSP packaging process, the FDZ193P minimizes both PCB space and $r_{DS(on)}$. This advanced WLCSP MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, ultra-low profile packaging, low gate charge, and low $r_{DS(on)}$.

Application

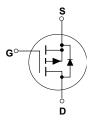
- Battery management
- Load switch
- Battery protection











MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DS}	Drain to Source Voltage		-20	V
V _{GS}	Gate to Source Voltage		±12	V
I _D	Drain Current -Continuous	(Note 1a)	-3	
	-Pulsed		-15	_ A
Б	Power Dissipation	(Note 1a)	1.9	10/
P_{D}	Power Dissipation	(Note 1b)	0.9	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	65	• C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	133	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
2	FDZ193P	WL-CSP	7"	8mm	5000 units

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, referenced to 25°C		-11		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -16V, V _{GS} = 0V			-1	μА
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 12V, V_{GS} = 0V$			±100	nA

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-0.6	-0.9	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250 μ A, referenced to 25°C		3		mV/°C
r _{DS(on)} Drain to Source		$V_{GS} = -4.5V, I_D = -1A$		66	90	
	Drain to Source On Resistance	$V_{GS} = -2.5V, I_{D} = -1A$		92	130	mΩ
		$V_{GS} = -1.7V, I_{D} = -1A$		195	300	
		$V_{GS} = -4.5V$, $I_D = -1A T_J = 125$ °C		84	123	
I _{D(on)}	On to State Drain Current	$V_{GS} = -4.5V, V_{DS} = -5V$	-10			Α
9 _{FS}	Forward Transconductance	$V_{DS} = -5V, I_{D} = -1A$		5.6		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 40V V - 0V	660	pF
C _{oss}	Output Capacitance	V _{DS} = -10V, V _{GS} = 0V, f = 1MHz	150	pF
C _{rss}	Reverse Transfer Capacitance	1 - NW12	90	pF
R_q	Gate Resistance	f = 1MHz	9.5	Ω

Switching Characteristics

	<u>-</u>				
t _{d(on)}	Turn-On Delay Time	1011	13	23	ns
t _r	Rise Time	$V_{DD} = -10V, I_{D} = -1A$ $V_{GS} = -4.5V, R_{GEN} = 6\Omega$	10	20	ns
t _{d(off)}	Turn-Off Delay Time	V _{GS} = -4.5V, N _{GEN} = 052	28	45	ns
t _f	Fall Time		21	34	ns
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0V \text{ to } 10V V_{DD} = -10V$	7	10	nC
Q_{gs}	Gate to Source Gate Charge	I _D = -1A	1		nC
Q _{ad}	Gate to Drain "Miller" Charge		2		nC

Drain-Source Diode Characteristics

I _S	Maximum continuous Drain-Source Diode Forward Current			-1.1	А
V_{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0V, I _S = -1.1A (Note 2)	-0.7	-1.2	V
t _{rr}	Reverse Recovery Time		19		ns
Q _{rr}	Reverse Recovery Charge	1 _F = -1A, αι/αι = 100A/μs	6		nC

Notes:

1: R_{0,0,A} is determined with the device mounted on a 1in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. The thermal resistance from the junction to the circuit board side of the solder ball, R_{0,0,B} is defined for reference. For R_{0,0,C} the thermal reference point for the case is defined as the top surface of the copper chip carrier. R_{0,0,C} and R_{0,0,B} are guaranteed by design while R_{0,0,A} is determined by the user's board design.



a. 65°C/W when mounted on a 1 in² pad of 2 oz copper,1.5" X 1.5" X 0.062" thick PCB



b. 133°C/W when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < $300\mu s$, Duty cycle < 2.0%.

Typical Characteristics T_J = 25°C unless otherwise noted

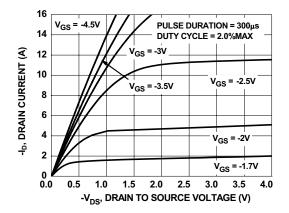


Figure 1. On Region Characteristics

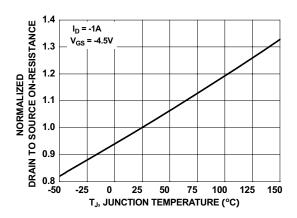


Figure 3. Normalized On Resistance vs Junction Temperature

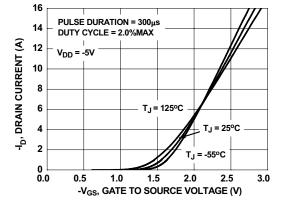


Figure 5. Transfer Characteristics

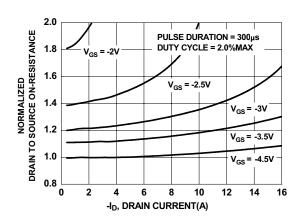


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

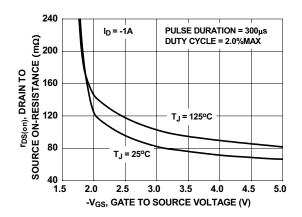


Figure 4. On-Resistance vs Gate to Source Voltage

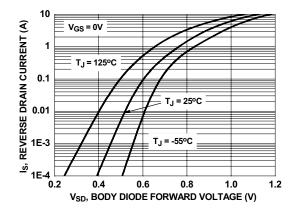


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

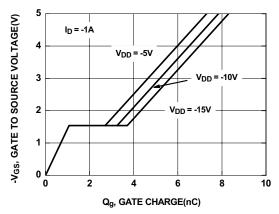


Figure 7. Gate Charge Characteristics

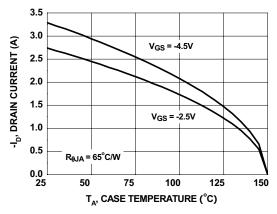


Figure 9. Maximum Continuous Drain Current vs Ambient Temperature

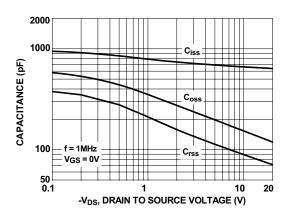


Figure 8. Capacitance vs Drain to Source Voltage

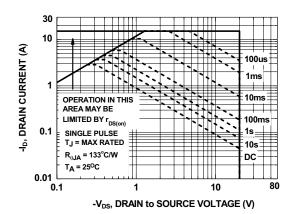


Figure 10. Forward Bias Safe Operating Area

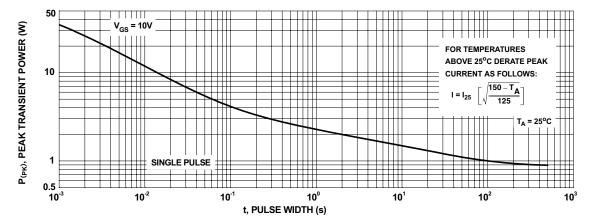


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

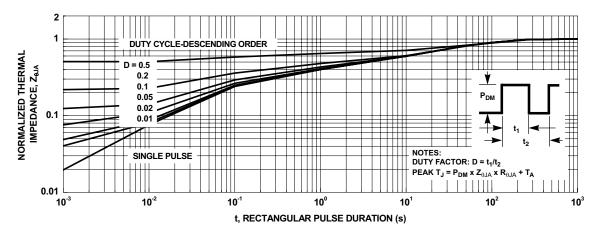
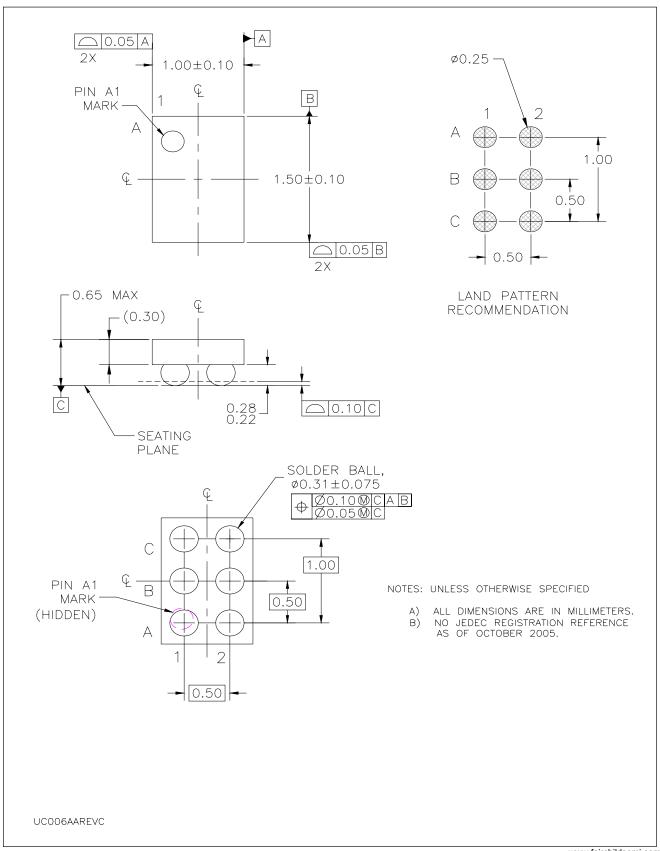


Figure 12. Transient Thermal Response Curve







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